



# 제25회 한국반도체학술대회

The 25<sup>th</sup> Korean Conference on Semiconductors

2018년 2월 5일(월)-7일(수), 강원도 하이원리조트 컨벤션 호텔

2018년 2월 7일(수), 09:00-10:30

Room C (함백, 5층)

## D. Thin Film Process Technology 분과

### [WC1-D] ALD/CVD Process (2D Materials)

좌장: 민요셉 교수(건국대학교), 한정환 교수(서울과학기술대학교)

<p><b>WC1-D-1</b> 09:00-09:15</p>	<p><b>Synthesis of 2-D SnS Thin Films and Their Potential Applications</b> In-Hwan Baek<sup>1,2</sup>, Jung Joon Pyeon<sup>1,3</sup>, Taek-Mo Chung<sup>4</sup>, Jeong Hwan Han<sup>5</sup>, Cheol Seong Hwang<sup>2</sup>, and Seong Keun Kim<sup>1</sup> <i><sup>1</sup>Center for Electronic Materials, KIST, <sup>2</sup>Department of Materials Science and Engineering, and Inter-University Semiconductor Research Center, Seoul National University, <sup>3</sup>KU-KIST Graduate School of Converging Science and Technology, <sup>4</sup>Division of Advanced Materials, KRICT, <sup>5</sup>Department of Materials Science and Engineering, Seoul National University of Science and Technology</i></p>
<p><b>WC1-D-2</b> 09:15-09:30</p>	<p><b>Characterizations of Charge-Trap Memory Thin-Film Transistors with HfO<sub>2</sub> Charge-Trap Layer Controlled by Atomic Layer Deposition Process</b> So-Yeong Na and Sung-Min Yoon <i>Department of Advanced Materials Engineering for Information and Electronics, Kyung Hee University</i></p>
<p><b>WC1-D-3</b> 09:30-09:45</p>	<p><b>Synthesis of 2-Dimensional Single Phase SnS<sub>2</sub> by Atomic Layer Deposition</b> Jung Joon Pyeon<sup>1,2</sup>, In-Hwan Baek<sup>1,3</sup>, Taek-Mo Chung<sup>4</sup>, Jeong Hwan Han<sup>5</sup>, Chong-Yun Kang<sup>1,2</sup>, Seong Keun Kim<sup>1</sup> <i><sup>1</sup>Center for Electronic Materials, KIST, <sup>2</sup>KU-KIST Graduate School of Converging Science and Technology, Korea University, <sup>3</sup>Department of Materials Science and Engineering, and Inter-university Semiconductor Research Center, Seoul National University, <sup>4</sup>Division of Advanced Materials, KRICT, <sup>5</sup>Department of Materials Science and Engineering, Seoul National University of Science and Technology</i></p>
<p><b>WC1-D-4</b> 09:45-10:00</p>	<p><b>Continuous and Ultrathin ALD Ru Film Deposition Using Discrete Feeding Method (DFM) and Electric Field Assisted ALD (EA-ALD)</b> Hyun Soo Jin and Tae Joo Park <i>Department of Materials Science and Chemical Engineering, Hanyang University</i></p>
<p><b>WC1-D-5</b> 10:00-10:15</p>	<p><b>Will Be Cubic BeO Thin Films the Next-Generation Dielectric?</b> Seong Keun Kim<sup>1</sup>, Woo Chul Lee<sup>1</sup>, Eric S. Larsen<sup>2,3</sup>, Jung Hwan Yum<sup>2,3</sup>, and Christopher W. Bielawski<sup>2,3</sup> <i><sup>1</sup>Center for Electronic Materials, KIST, <sup>2</sup>Department of Chemistry and Engineering, UNIST, <sup>3</sup>Center for Multidimensional Carbon Materials (CMCM), Institute for Basic Science (IBS)</i></p>
<p><b>WC1-D-6</b> 10:15-10:30</p>	<p><b>High Growth Rate (&gt; 0.25 nm/cycle) of Plasma-Enhanced Atomic-Layer-Deposited SiON Thin Film Using ICP Type Remote Plasma</b> Dae Hyun Kim<sup>1</sup>, Han Jin Lee<sup>2</sup>, Hyun Soo Jin<sup>2</sup>, Hyung Kun Lee<sup>3</sup>, Jeongsik Kim<sup>3</sup>, Min Ja Yoo<sup>3</sup>, Taewook Kim<sup>3</sup>, Jun Young Kim<sup>3</sup>, Mingun Lee<sup>3</sup>, Kyu Sung Cho<sup>3</sup>, Jae Woo Lee<sup>3</sup>, Jaehyun Kim<sup>3</sup>, and Tae Joo Park<sup>1,2</sup> <i><sup>1</sup>Department of Advanced Materials Engineering, Hanyang University, <sup>2</sup>Department of Materials Science and Chemical Engineering, Hanyang University, <sup>3</sup>Electronic Materials Business Division III, Dongjin Semichem</i></p>